

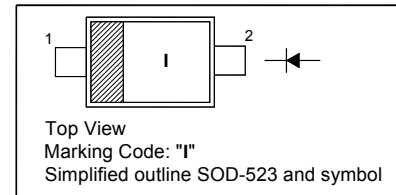
1N6263WT

SILICON SCHOTTKY BARRIER DIODE

for general purpose applications

PINNING

PIN	DESCRIPTION
1	Cathode
2	Anode

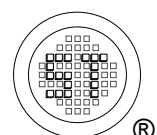


Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

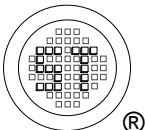
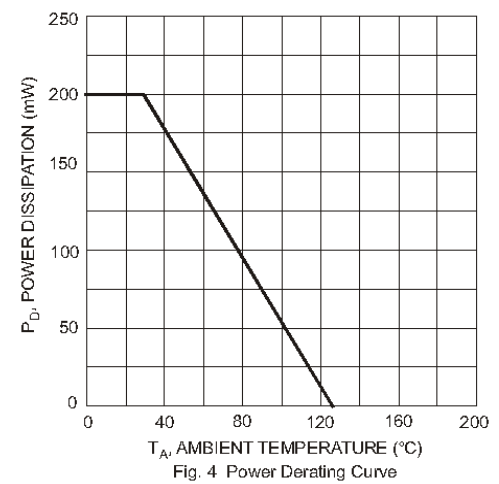
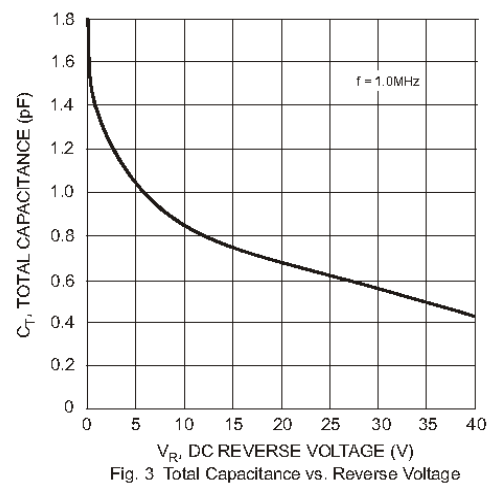
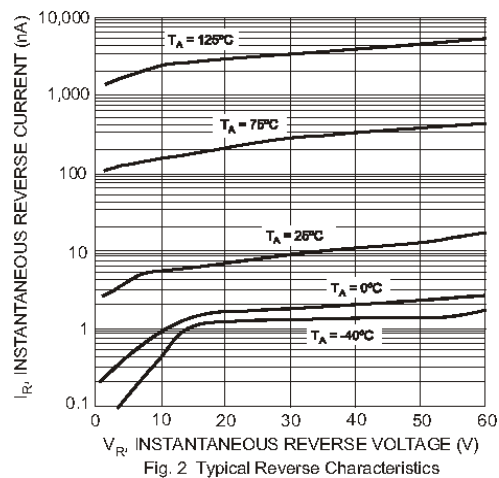
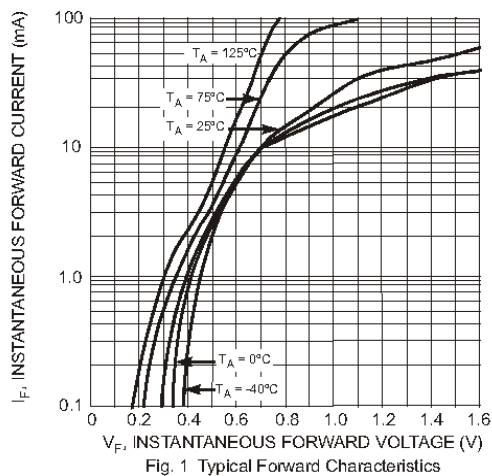
Parameter	Symbol	Value	Unit
Peak Repetitive Reverse Voltage	V_{RRM}	60	V
Reverse Voltage	V_R	60	V
Forward Continuous Current	I_{FM}	15	mA
Power Dissipation	P_d	200	mW
Non-Repetitive Peak Forward Surge Current	I_{FSM}	50 2	mA A
Operating and Storage Temperature Range	T_j, T_{stg}	- 55 to + 125	$^\circ\text{C}$

Characteristics at $T_a = 25^\circ\text{C}$

Parameter	Symbol	Min.	Max.	Unit
Reverse Breakdown Voltage at $I_R = 10\ \mu\text{A}$	$V_{(BR)R}$	60	-	V
Forward Voltage at $I_F = 1\ \text{mA}$ at $I_F = 15\ \text{mA}$	V_F	- -	0.41 1	V
Reverse Current at $V_R = 50\ \text{V}$	I_R	-	200	nA
Total Capacitance at $V_R = 0\ \text{V}$, $f = 1\ \text{MHz}$	C_T	-	2	pF
Reverse Recovery Time at $I_F = I_R = 5\ \text{mA}$, $I_{rr} = 0.1 \times I_R$, $R_L = 100\ \Omega$	t_{rr}	-	1	ns



Dated : 23/11/2006

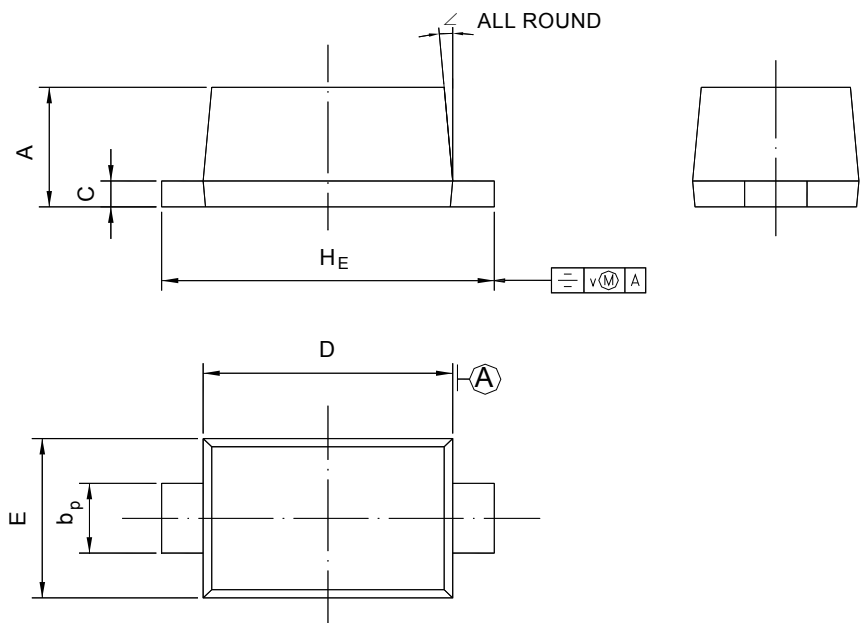


1N6263WT

PACKAGE OUTLINE

Plastic surface mounted package; 2 leads

SOD-523



UNIT	A	b _p	C	D	E	H _E	V	∠
mm	0.70 0.60	0.4 0.3	0.135 0.100	1.25 1.15	0.85 0.75	1.7 1.5	0.1	5°

